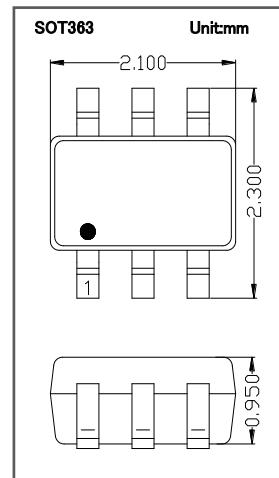
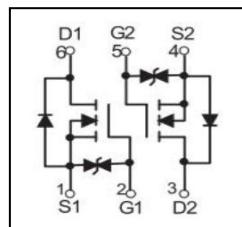


- ◇ Epoxy Meets UL 94 V-0 Flammability Rating
- ◇ High Density Cell Design For Low $R_{DS(ON)}$
- ◇ Voltage Controlled Small Signal Switch
- ◇ Rugged And Reliable
- ◇ ESD Protected

Device Marking Code	
CJ3134KDW	34K

Equivalent Circuit



Maximum Ratings ($T_a = 25^\circ C$)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source-Voltage	± 8	V
I_D	Drain Current – Continuous ($t \leq 10s$)	0.75	A
P_d	Total Power Dissipation*	0.15	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-55 to 150	$^\circ C$
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	833	$^\circ C/W$

*Pulse Width Limited By Junction Temperature.

Electrical Characteristics ($T_a = 25^\circ C$)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20			V
$V_{GS(th)}$	Gate-Threshold Voltage ^(Note1)	$V_{DS}=V_{GS}, I_D=250\mu A$	0.3	0.54	1.1	V
I_{GSS}	Gate-Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 8V$			± 10	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$			1	μA
$R_{DS(ON)}$	Drain-Source On-Resistance ^(Note1)	$V_{GS}=4.5V, I_D=0.65A$		270	380	$m \Omega$
		$V_{GS}=2.5V, I_D=0.55A$		320	450	
		$V_{GS}=1.8V, I_D=0.45A$		390	800	
V_{SD}	Diode Forward Voltage ^(Note1)	$V_{GS}=0V, I_S=0.15A$			1.2	V
g_{FS}	Forward Transconductance ^(Note1)	$V_{DS}=10V, I_D=0.8A$		1.6		S

Dynamic Characteristics (Note2)

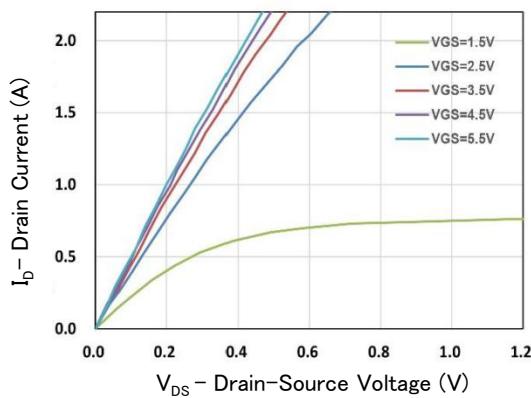
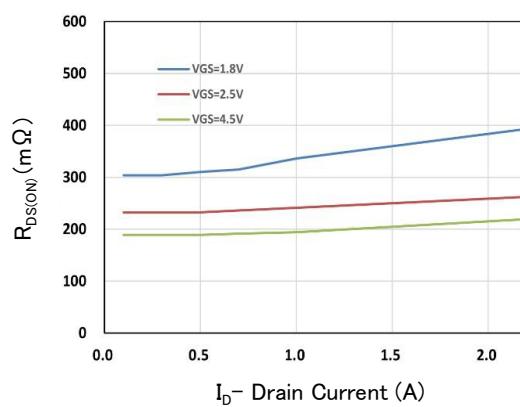
C _{iss}	Input Capacitance	$V_{DS}=10V$ $V_{GS}=0V$ $f=1MHz$	43		pF
C _{oss}	Output Capacitance		9		
C _{rss}	Reverse Transfer Capacitance		6		

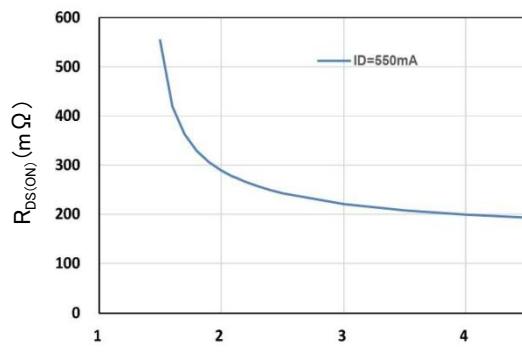
Switching Parameters (Note2)

T _{d(on)}	Turn-On Delay Time	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=2A, R_{GEN}=6\Omega$	1.2		nS
t _r	Turn-On Rise Time		25		
T _{d(off)}	Turn-Off Delay Time		14		
t _f	Turn-Off Fall Time		15		
Q _g	Total Gate Charge	$V_{DS}=10V, V_{GS}=4.5V, I_D=1A$	2		nC
Q _{gs}	Gate-Source Charge		0.3		
Q _{gd}	Gate-Drain Charge		0.3		

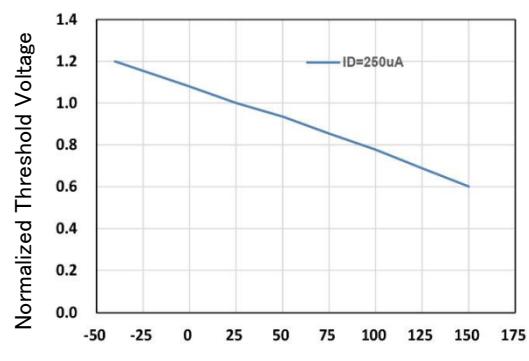
Notes:

1. Pulse Test: Pulse Width≤300us, Duty Cycle≤0.5%
2. Guaranteed By Design, Not Subject To Production Testing.

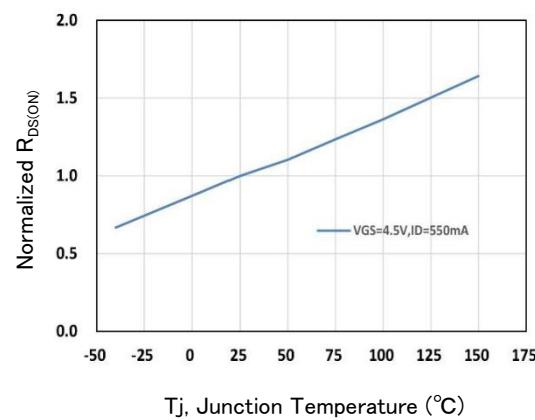
Typical Characteristics

Output Characteristics

On-Resistance vs. ID



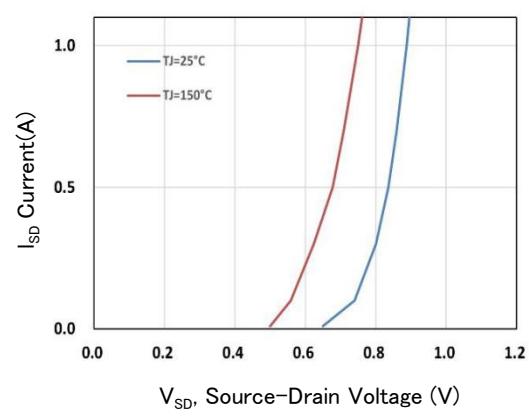
On-Resistance vs. V_{GS}



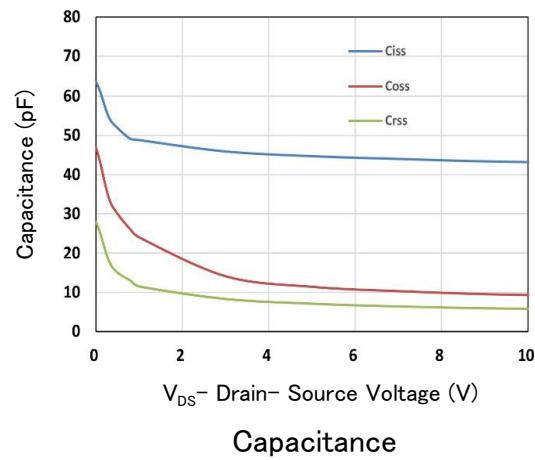
Gate Threshold Voltage



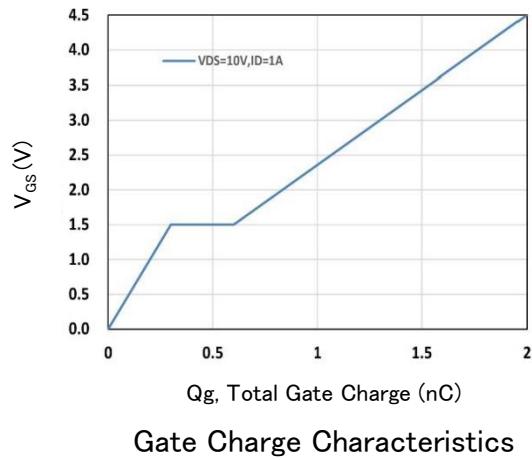
Drain-Source On Resistance



Source-Drain Diode Forward



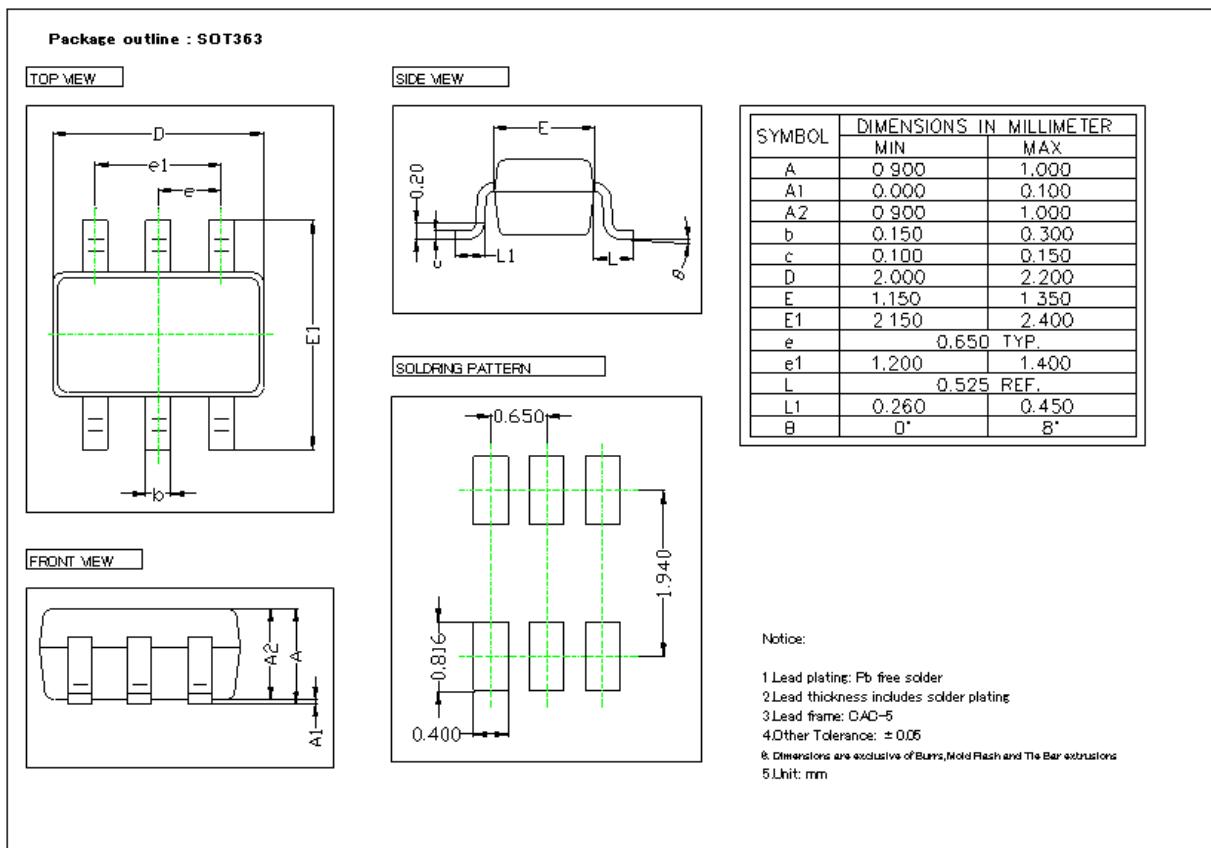
Capacitance



Gate Charge Characteristics

Ordering Information

Device	Package	Shipping	Tape wide	Emboss pitch	Tape specification	Notes
CJ3134KDW	SOT363	Tape & Reel 3000pcs /7" Reel	8mm	4mm	Conductive	

Package Dimensions


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